

FEATURES

- ±2 V to ±6 V dual supply
- 2 V to 12 V single supply
- Automotive temperature range –40°C to +125°C
- <0.1 nA leakage currents
- 45 Ω on resistance over full signal range
- Rail-to-rail switching operation
- Single 8-to-1 multiplexer ADG658
- Differential 4-to-1 multiplexer ADG659
- 16-lead LFCSP/TSSOP/QSOP packages
- Typical power consumption <0.1 μW
- TTL/CMOS compatible inputs
- Package upgrades to 74HC4051/74HC4052 and
MAX4051/MAX4052/MAX4581/MAX4582

APPLICATIONS

- Automotive applications
- Automatic test equipment
- Data acquisition systems
- Battery-powered systems
- Communication systems
- Audio and video signal routing
- Relay replacement
- Sample-and-hold systems
- Industrial control systems

GENERAL DESCRIPTION

The ADG658 and ADG659 are low voltage, CMOS analog multiplexers comprised of eight single channels and four differential channels, respectively. The ADG658 switches one of eight inputs (S1–S8) to a common output, D, as determined by the 3-bit binary address lines A0, A1, and A2. The ADG659 switches one of four differential inputs to a common differential output, as determined by the 2-bit binary address lines A0 and A1. An $\overline{\text{EN}}$ input on both devices is used to enable or disable the device. When disabled, all channels are switched off.

These parts are designed on an enhanced process that provides lower power dissipation yet gives high switching speeds. These parts can operate equally well as either multiplexers or demultiplexers and have an input range that extends to the supplies. All channels exhibit break-before-make switching action, preventing momentary shorting when switching channels. All digital inputs have 0.8 V to 2.4 V logic thresholds, ensuring TTL/CMOS logic compatibility when using single +5 V or dual ±5 V supplies.

Rev. B

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FUNCTIONAL BLOCK DIAGRAM

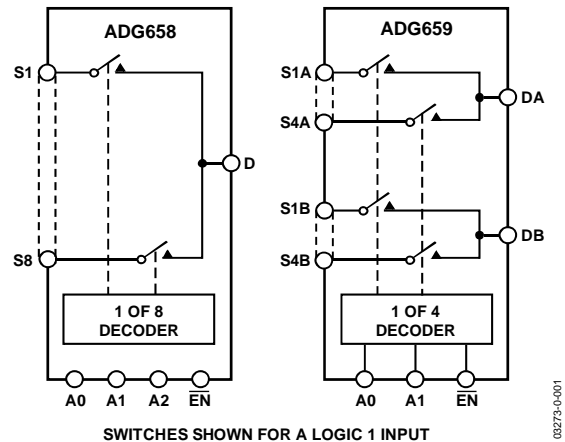


Figure 1.

The ADG658 and ADG659 are available in 16-lead TSSOP/QSOP packages and 16-lead 4 mm × 4 mm LFCSP packages.

PRODUCT HIGHLIGHTS

1. Single- and dual-supply operation. The ADG658 and ADG659 offer high performance and are fully specified and guaranteed with ±5 V, +5 V, and +3 V supply rails.
2. Automotive temperature range –40°C to +125°C.
3. Low power consumption, typically <0.1 μW.
4. 16-lead 4 mm × 4 mm LFCSP packages, 16-lead TSSOP package and 16-lead QSOP package.

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REVISION HISTORY

2/09—Rev. A to Rev. B

Changes to Ordering Guide	20
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7/04—Rev. 0 to Rev. A

Updated Format	Universal
Added QSOP Package Outline	20
Changes to Ordering Guide	20

3/03—Rev. 0: Initial Version

SPECIFICATIONS

DUAL SUPPLY

$V_{DD} = +5\text{ V} \pm 10\%$, $V_{SS} = -5\text{ V} \pm 10\%$, $GND = 0\text{ V}$, unless otherwise noted.

Table 1.

Parameter	B Version		Y Version	Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH					
Analog Signal Range			V_{SS} to V_{DD}	V	$V_{DD} = +4.5\text{ V}$, $V_{SS} = -4.5\text{ V}$
On Resistance (R_{ON})	45			Ω typ	$V_S = \pm 4.5\text{ V}$, $I_S = 1\text{ mA}$; see Figure 21
	75	90	100	Ω max	
On Resistance Match between Channels (ΔR_{ON})	1.3			Ω typ	$V_S = 3.5\text{ V}$, $I_S = 1\text{ mA}$
	3	3.2	3.5	Ω max	$V_{DD} = +5\text{ V}$, $V_{SS} = -5\text{ V}$;
On Resistance Flatness ($R_{FLAT(ON)}$)	10			Ω typ	$V_S = \pm 3\text{ V}$, $I_S = 1\text{ mA}$
	16	17	18	Ω max	
LEAKAGE CURRENTS					
Source OFF Leakage I_S (OFF)	± 0.005			nA typ	$V_{DD} = +5.5\text{ V}$, $V_{SS} = -5.5\text{ V}$
	± 0.2		± 5	nA max	$V_D = \pm 4.5\text{ V}$, $V_S = \mp 4.5\text{ V}$; see Figure 22
Drain OFF Leakage I_D (OFF)	± 0.005			nA typ	$V_D = \pm 4.5\text{ V}$, $V_S = \mp 4.5\text{ V}$; see Figure 23
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
Channel ON Leakage I_D, I_S (ON)	± 0.005			nA typ	$V_D = V_S = \pm 4.5\text{ V}$; see Figure 24
ADG658	± 0.2		± 5	nA max	
ADG659	± 0.1		± 2.5	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.4	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current					
I_{INL} or I_{INH}	0.005			μA typ	$V_{IN} = V_{INL}$ or V_{INH}
			± 1	μA max	
C_{IN} , Digital Input Capacitance	2			pF typ	
DYNAMIC CHARACTERISTICS¹					
$t_{TRANSITION}$	80			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	115	140	165	ns max	$V_S = 3\text{ V}$; see Figure 25
$t_{ON}(\overline{EN})$	80			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	115	140	165	ns max	$V_S = 3\text{ V}$; see Figure 27
$t_{OFF}(\overline{EN})$	30			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	45	50	55	ns max	$V_S = 3\text{ V}$; see Figure 27
Break-Before-Make Time Delay, t_{BBM}	50			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
			10	ns min	$V_{S1} = V_{S2} = 3\text{ V}$; see Figure 26
Charge Injection	2			pC typ	$V_S = 0\text{ V}$, $R_S = 0\ \Omega$,
	4			pC max	$C_L = 1\text{ nF}$; see Figure 28
Off Isolation	-90			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 29
Total Harmonic Distortion, THD + N	0.025			% typ	$R_L = 600\ \Omega$, 2 V p-p , $f = 20\text{ Hz}$ to 20 kHz
Channel-to-Channel Crosstalk (ADG659)	-90			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 31
-3 dB Bandwidth					
ADG658	210			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 30
ADG659	400			MHz typ	

ADG658/ADG659

Parameter	B Version		Y Version	Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	-40°C to +125°C		
C _S (OFF)	4			pF typ	f = 1 MHz
C _D (OFF)					
ADG658	23			pF typ	f = 1 MHz
ADG659	12			pF typ	f = 1 MHz
C _D , C _S (ON)					
ADG658	28			pF typ	f = 1 MHz
ADG659	16			pF typ	f = 1 MHz
POWER REQUIREMENTS					
I _{DD}	0.01			μA typ	V _{DD} = +5.5 V, V _{SS} = -5.5 V Digital Inputs = 0 V or 5.5 V
			1	μA max	
I _{SS}	0.01			μA typ	Digital Inputs = 0 V or 5.5 V
			1	μA max	

¹ Guaranteed by design; not subject to production test.

5 V SINGLE SUPPLY

$V_{DD} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 2.

Parameter	B Version			Y Version		Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	-40°C to +125°C	-40°C	-40°C to +125°C		
ANALOG SWITCH							
Analog Signal Range				0 to V_{DD}		V	$V_{DD} = 4.5\text{ V}$, $V_{SS} = 0\text{ V}$
On Resistance (R_{ON})	85					Ω typ	$V_S = 0\text{ V}$ to 4.5 V , $I_S = 1\text{ mA}$; see Figure 21
	150	160	200			Ω max	
On Resistance Match between Channels (ΔR_{ON})	4.5					Ω typ	$V_S = 3.5\text{ V}$, $I_S = 1\text{ mA}$
	8	9	10			Ω max	
On Resistance Flatness ($R_{FLAT(ON)}$)	13	14	16			Ω typ	$V_{DD} = 5\text{ V}$, $V_{SS} = 0\text{ V}$, $V_S = 1.5\text{ V}$ to 4 V , $I_S = 1\text{ mA}$
LEAKAGE CURRENTS							
Source OFF Leakage I_S (OFF)	± 0.005					nA typ	$V_{DD} = 5.5\text{ V}$
	± 0.2			± 5		nA max	$V_S = 1\text{ V}/4.5\text{ V}$, $V_D = 4.5\text{ V}/1\text{ V}$; see Figure 22
Drain OFF Leakage I_D (OFF)	± 0.005					nA typ	$V_S = 1\text{ V}/4.5\text{ V}$, $V_D = 4.5\text{ V}/1\text{ V}$; see Figure 23
ADG658	± 0.2			± 5		nA max	
ADG659	± 0.1			± 2.5		nA max	
Channel ON Leakage I_D , I_S (ON)	± 0.005					nA typ	$V_S = V_D = 1\text{ V}$ or 4.5 V , see Figure 24
ADG658	± 0.2			± 5		nA max	
ADG659	± 0.1			± 2.5		nA max	
DIGITAL INPUTS							
Input High Voltage, V_{INH}				2.4		V min	
Input Low Voltage, V_{INL}				0.8		V max	
Input Current							
I_{INL} or I_{INH}	0.005					μA typ	$V_{IN} = V_{INL}$ or V_{INH}
				± 1		μA max	
C_{IN} , Digital Input Capacitance	2					pF typ	
DYNAMIC CHARACTERISTICS¹							
$t_{TRANSITION}$	120					ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	200	270	300			ns max	$V_S = 3\text{ V}$; see Figure 25
$t_{ON}(\overline{EN})$	120					ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	190	245	280			ns max	$V_S = 3\text{ V}$; see Figure 27
$t_{OFF}(\overline{EN})$	35					ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	50	60	70			ns max	$V_S = 3\text{ V}$; see Figure 27
Break-Before-Make Time Delay, t_{BBM}	100					ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
				10		ns min	$V_{S1} = V_{S2} = 3\text{ V}$; see Figure 26
Charge Injection	0.5					pC typ	$V_S = 2.5\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 28
	1					pC max	
Off Isolation	-90					dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 29
Channel-to-Channel Crosstalk (ADG659)	-90					dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; $f = 1\text{ MHz}$; see Figure 31
-3 dB Bandwidth							
ADG658	180					MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 30
ADG659	330					MHz typ	
C_S (OFF)	5					pF typ	$f = 1\text{ MHz}$
C_D (OFF)							
ADG658	29					pF typ	$f = 1\text{ MHz}$
ADG659	15					pF typ	$f = 1\text{ MHz}$

ADG658/ADG659

Parameter	B Version		Y Version	Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	-40°C to +125°C		
C _D , C _S (ON)					
ADG658	30			pF typ	f = 1 MHz
ADG659	16			pF typ	f = 1 MHz
POWER REQUIREMENTS					V _{DD} = 5.5 V
I _{DD}	0.01		1	μA typ μA max	Digital Inputs = 0 V or 5.5 V

¹ Guaranteed by design; not subject to production test.

2.7 V TO 3.6 V SINGLE SUPPLY

V_{DD} = 2.7 to 3.6 V, V_{SS} = 0 V, GND = 0 V, unless otherwise noted.

Table 3.

Parameter	B Version			Y Version		Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	-40°C to +125°C	-40°C to +125°C	-40°C to +125°C		
ANALOG SWITCH							
Analog Signal Range				0 to V _{DD}		V	V _{DD} = 2.7 V, V _{SS} = 0 V
On Resistance (R _{ON})	185					Ω typ	V _S = 0 V to 2.7 V, I _S = 0.1 mA; see Figure 21
	300	350		400		Ω max	
On Resistance Match between Channels (ΔR _{ON})	2					Ω typ	V _S = 1.5 V, I _S = 0.1 mA
	4.5	6		7		Ω max	
LEAKAGE CURRENTS							
Source OFF Leakage I _S (OFF)	±0.005					nA typ	V _{DD} = 3.3 V
	±0.2			±5		nA max	V _S = 1 V/3 V, V _D = 3 V/1 V; see Figure 22
Drain OFF Leakage I _D (OFF)	±0.005					nA typ	V _S = 1 V/3 V, V _D = 3 V/1 V; see Figure 23
ADG658	±0.2			±5		nA max	
ADG659	±0.1			±2.5		nA max	
Channel ON Leakage I _D , I _S (ON)	±0.005					nA typ	V _S = V _D = 1 V or 3 V, see Figure 24
ADG658	±0.2			±5		nA max	
ADG659	±0.1			±2.5		nA max	
DIGITAL INPUTS							
Input High Voltage, V _{INH}				2.0		V min	
Input Low Voltage, V _{INL}				0.5		V max	
Input Current							
I _{INL} or I _{INH}	0.005					μA typ	V _{IN} = V _{INL} or V _{INH}
				±1		μA max	
C _{IN} , Digital Input Capacitance	2					pF typ	
DYNAMIC CHARACTERISTICS¹							
t _{TRANSITION}	200					ns typ	R _L = 300 Ω, C _L = 35 pF
	370	440		490		ns max	V _S = 1.5 V; see Figure 25
t _{ON} ($\overline{\text{EN}}$)	230					ns typ	R _L = 300 Ω, C _L = 35 pF
	370	440		490		ns max	V _S = 1.5 V; see Figure 27
t _{OFF} ($\overline{\text{EN}}$)	50					ns typ	R _L = 300 Ω, C _L = 35 pF
	80	90		110		ns max	V _S = 1.5 V; see Figure 27
Break-Before-Make Time Delay, t _{BBM}	200					ns typ	R _L = 300 Ω, C _L = 35 pF
				10		ns min	V _{S1} = V _{S2} = 1.5 V; see Figure 26
Charge Injection	1					pC typ	V _S = 1.5 V, R _S = 0 Ω, C _L = 1 nF; see Figure 28
	2					pC max	
Off Isolation	-90					dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; see Figure 29
Channel-to-Channel Crosstalk (ADG659)	-90					dB typ	R _L = 50 Ω, C _L = 5 pF; f = 1 MHz; see Figure 31
-3 dB Bandwidth							
ADG658	160					MHz typ	R _L = 50 Ω, C _L = 5 pF; see Figure 30
ADG659	300					MHz typ	
C _S (OFF)	5					pF typ	f = 1 MHz
C _D (OFF)							
ADG658	29					pF typ	f = 1 MHz
ADG659	15					pF typ	f = 1 MHz

ADG658/ADG659

Parameter	B Version		Y Version	Unit	Test Conditions/Comments
	+25°C	-40°C to +85°C	-40°C to +125°C		
C _D , C _S (ON)					
ADG658	30			pF typ	f = 1 MHz
ADG659	16			pF typ	f = 1 MHz
POWER REQUIREMENTS					V _{DD} = 3.6 V
I _{DD}	0.01		1	μA typ μA max	Digital Inputs = 0 V or 3.6 V

¹ Guaranteed by design; not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameter	Rating
V_{DD} to V_{SS}	13 V
V_{DD} to GND	-0.3 V to +13 V
V_{SS} to GND	+0.3 V to -6.5 V
Analog Inputs ¹	$V_{SS} - 0.3\text{ V}$ to $V_{DD} + 0.3\text{ V}$
Digital Inputs ¹	GND - 0.3 V to $V_{DD} + 0.3\text{ V}$ or 10 mA, whichever occurs first
Peak Current, S or D (Pulsed at 1 ms, 10% duty cycle max)	40 mA
Continuous Current, S or D	20 mA
Operating Temperature Range	
Automotive (Y Version)	-40°C to +125°C
Industrial (B Version)	-40°C to +85°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature	150°C
θ_{JA} Thermal Impedance	
16-Lead QSOP	104°C/W
16-Lead TSSOP	150.4°C/W
16-Lead LFCSP (4-Layer Board)	70°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
ESD	5.5 kV

¹ Over voltages at A_x , \overline{EN} , S, or D are clamped by internal diodes. Current should be limited to the maximum ratings.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

ADG658/ADG659

Table 5. ADG658 Truth Table

A2	A1	A0	$\overline{\text{EN}}$	Switch Condition
X ¹	X ¹	X ¹	1	None
0	0	0	0	1
0	0	1	0	2
0	1	0	0	3
0	1	1	0	4
1	0	0	0	5
1	0	1	0	6
1	1	0	0	7
1	1	1	0	8

¹X = Don't Care

Table 6. ADG659 Truth Table

A1	A0	$\overline{\text{EN}}$	On Switch Pair
X ¹	X ¹	1	None
0	0	0	1
0	1	0	2
1	0	0	3
1	1	0	4

¹X = Don't Care

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

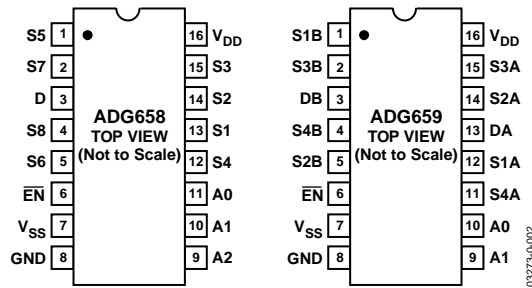


Figure 2. 16-Lead TSSOP/QSOP Pin Configuration

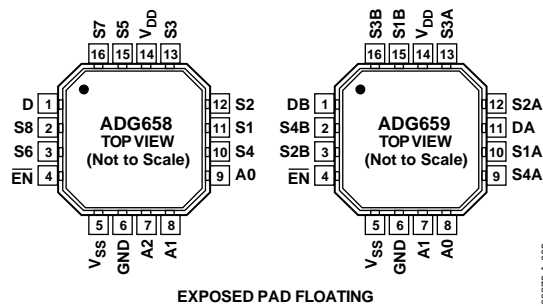


Figure 3. 16-Lead, 4 mm x 4 mm LFCSP Pin Configuration

Table 7. Pin Function Descriptions

Parameter	Description
V _{DD}	Most Positive Power Supply Potential.
V _{SS}	Most Negative Power Supply Potential.
I _{DD}	Positive Supply Current.
I _{SS}	Negative Supply Current.
GND	Ground (0 V) Reference.
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
A _X	Logic Control Input.
EN	Active Low Digital Input. When high, device is disabled and all switches are OFF. When low, A _x logic inputs determine ON switch.
V _D (V _s)	Analog Voltage on Terminals D, S.
R _{ON}	Ohmic Resistance between D and S.
ΔR _{ON}	On Resistance Match between Any Two Channels, i.e., R _{ONmax} – R _{ONmin} .
R _{FLAT(ON)}	Flatness is defined as the difference between the maximum and minimum value of ON Resistance as measured over the specified analog signal range.
I _S (OFF)	Source Leakage Current with the Switch OFF.
I _D (OFF)	Drain Leakage Current with the Switch OFF.
I _D , I _S (ON)	Channel Leakage Current with the Switch ON.
V _{INL}	Maximum Input Voltage for Logic 0.
V _{INH}	Minimum Input Voltage for Logic 1.
I _{INL} (I _{INH})	Input Current of the Digital Input.
C _S (OFF)	OFF Switch Source Capacitance. Measured with reference to ground.
C _D (OFF)	OFF Switch Drain Capacitance. Measured with reference to ground.
C _D , C _S (ON)	ON Switch Capacitance. Measured with reference to ground.
C _{IN}	Digital Input Capacitance.

ADG658/ADG659

Parameter	Description
t_{ON}	Delay between Applying the Digital Control Input and the Output Switching ON. See Test Circuit 7.
t_{OFF}	Delay between Applying the Digital Control Input and the Output Switching OFF.
t_{BBM}	ON Time. Measured between 80% points of both switches when switching from one address state to another.
Charge Injection	Measure of the Glitch Impulse Transferred from the Digital Input to the Analog Output during Switching.
Off Isolation	Measure of Unwanted Signal Coupling through an OFF Switch.
Crosstalk	Measure of Unwanted Signal Coupled through from One Channel to Another as a Result of Parasitic Capacitance.
Bandwidth	The Frequency at which the Output is Attenuated by 3 dB.
On Response	The Frequency Response of the ON Switch.
Insertion Loss	The Loss Due to the ON Resistance of the Switch.

TYPICAL PERFORMANCE CHARACTERISTICS

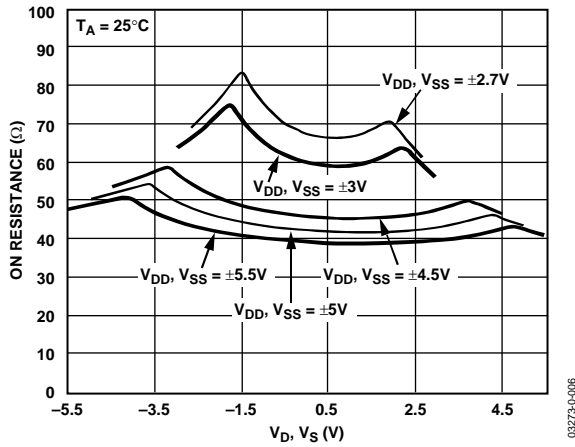


Figure 4. On Resistance vs. V_D (V_S) for Dual Supply

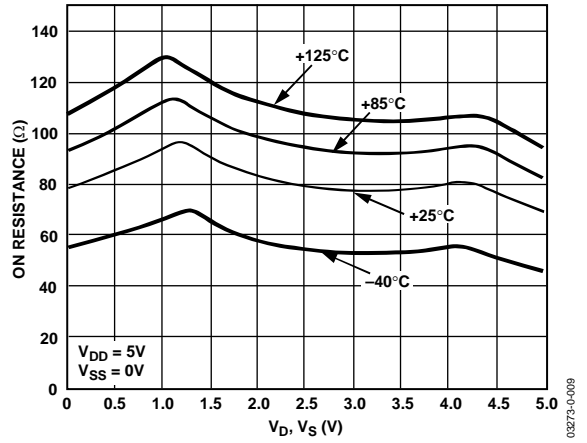


Figure 7. On Resistance vs. V_D (V_S) for Different Temperatures (Single Supply)

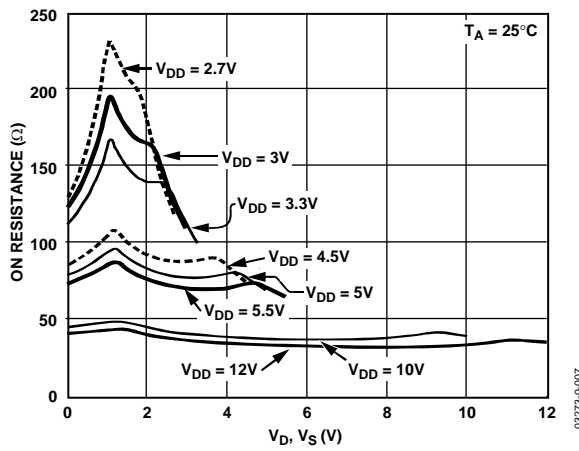


Figure 5. On Resistance vs. V_D (V_S) for Single Supply

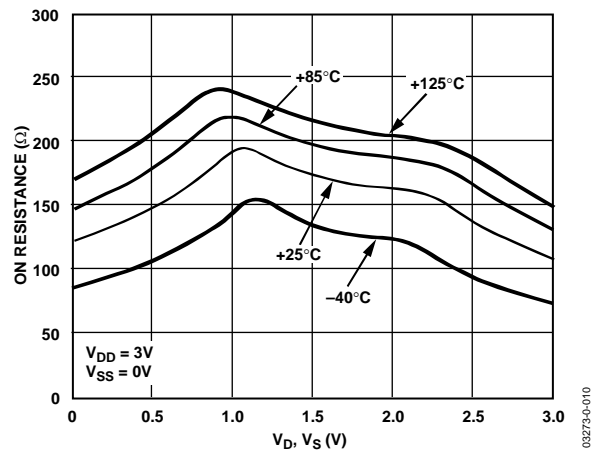


Figure 8. On Resistance vs. V_D (V_S) for Different Temperatures (Single Supply)

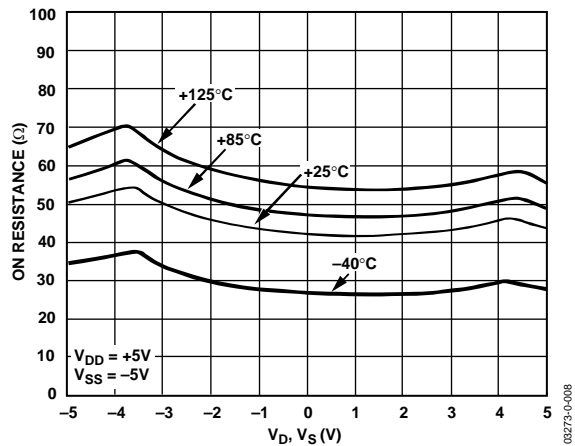


Figure 6. On Resistance vs. V_D (V_S) for Different Temperatures (Dual Supply)

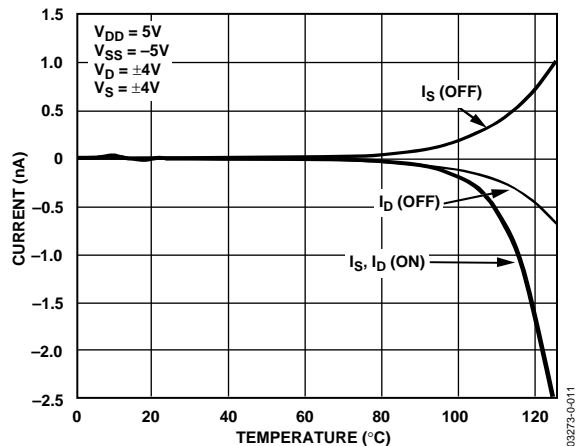


Figure 9. Leakage Current vs. Temperature (Dual Supply)

ADG658/ADG659

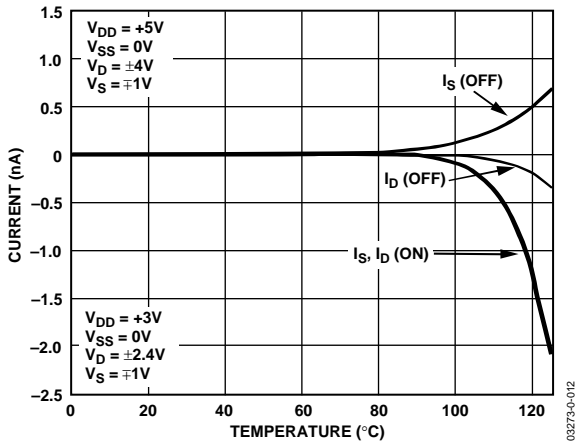


Figure 10. Leakage Current vs. Temperature (Single Supply)

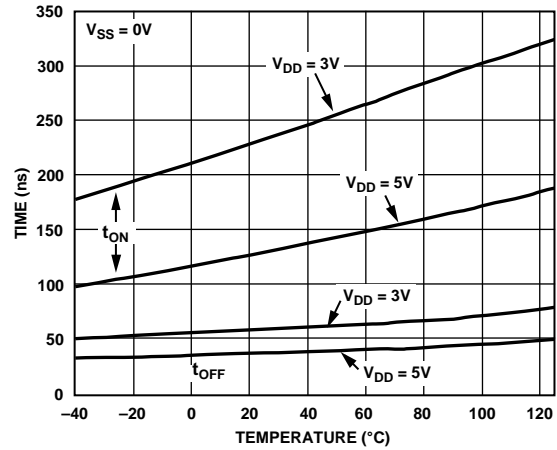


Figure 13. t_{ON}/t_{OFF} Times vs. Temperature (Single Supply)

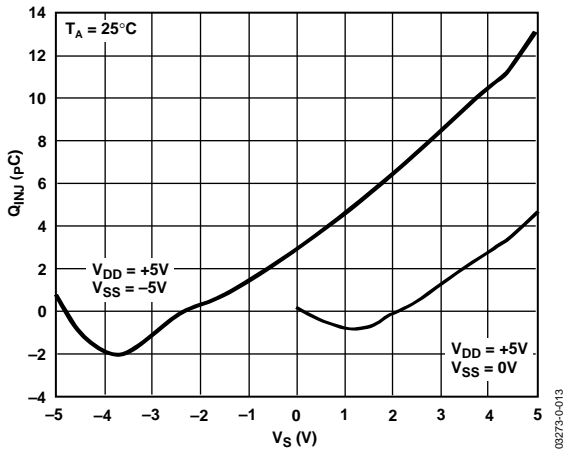


Figure 11. Charge Injection vs. Source Voltage

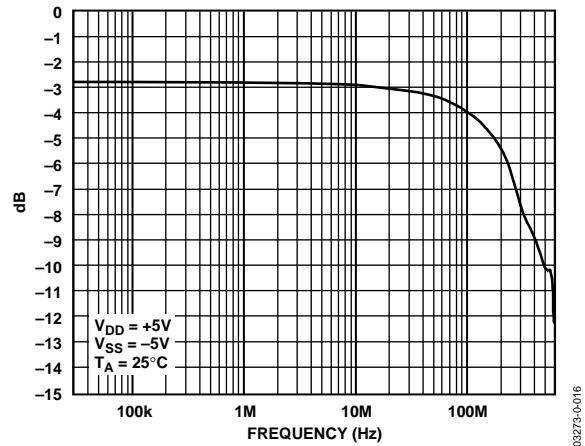


Figure 14. ON Response vs. Frequency (ADG658)

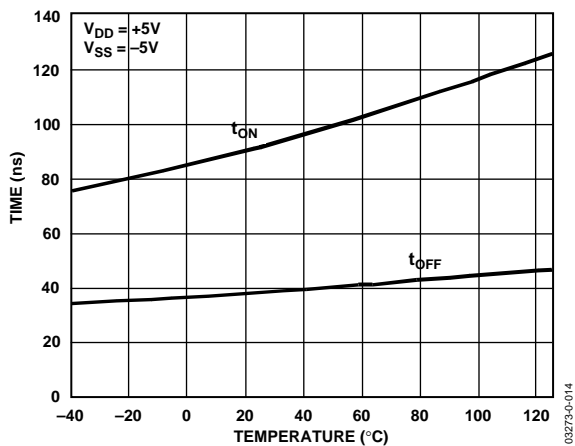


Figure 12. t_{ON}/t_{OFF} Times vs. Temperature (Dual Supply)

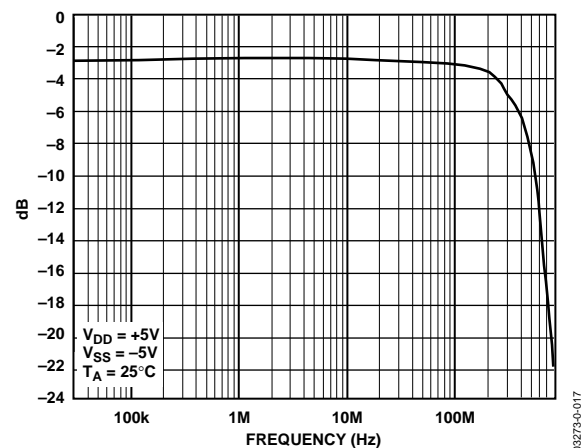


Figure 15. ON Response vs. Frequency (ADG659)

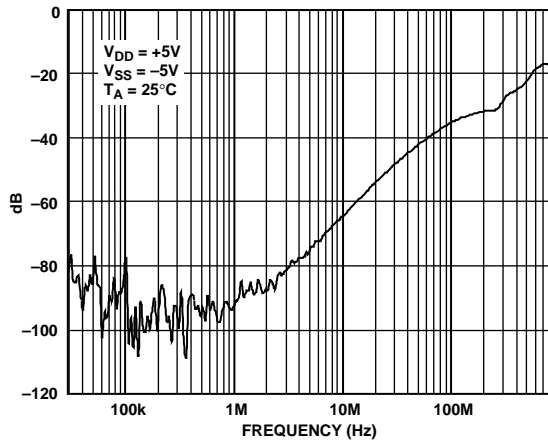


Figure 16. OFF Isolation vs. Frequency

03273-0-018

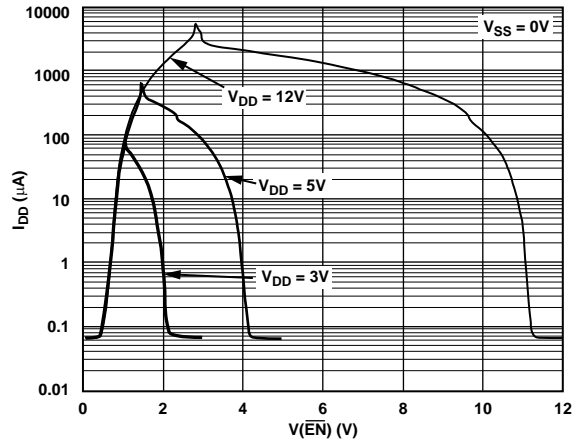


Figure 19. V_{DD} Current vs. Logic Level

03273-0-021

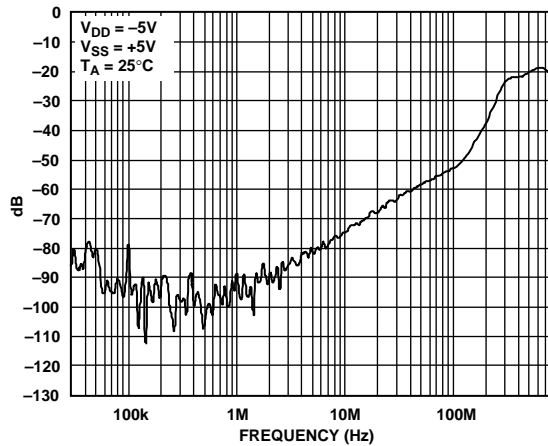


Figure 17. Crosstalk vs. Frequency

03273-0-019

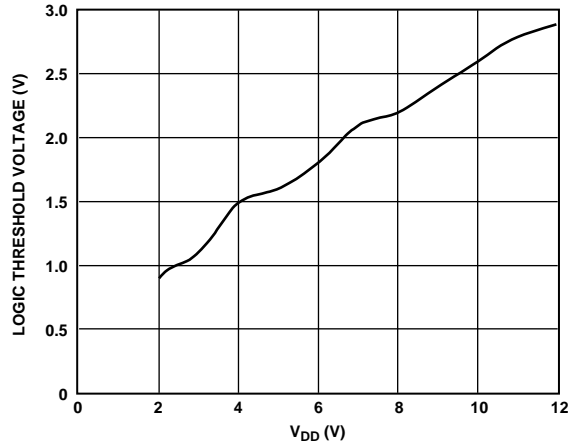


Figure 20. Logic Threshold Voltage vs. Supply Voltage

03273-0-022

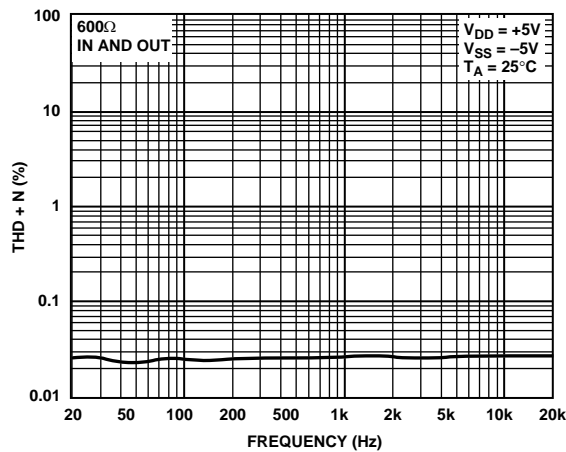


Figure 18. THD + Noise

03273-0-020

TEST CIRCUITS

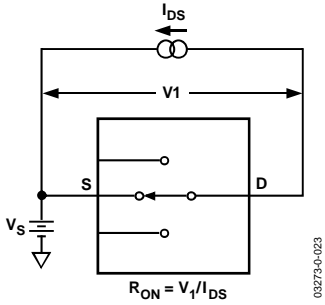


Figure 21. ON Resistance

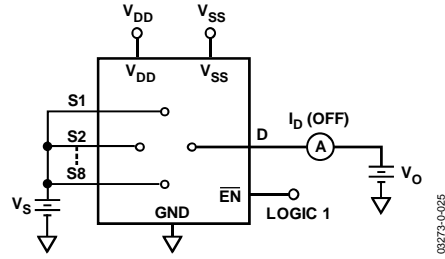


Figure 23. I_D (OFF)

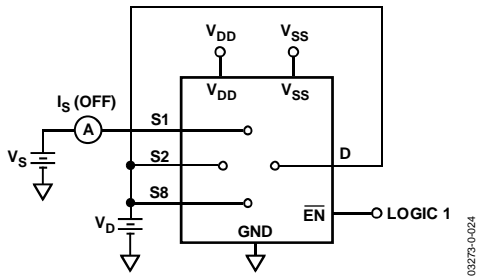


Figure 22. I_S (OFF)

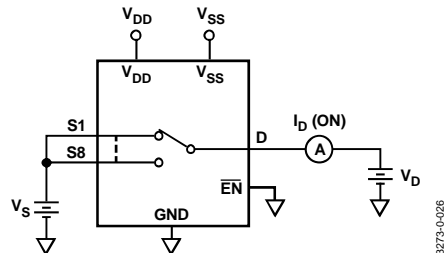


Figure 24. I_D (ON)

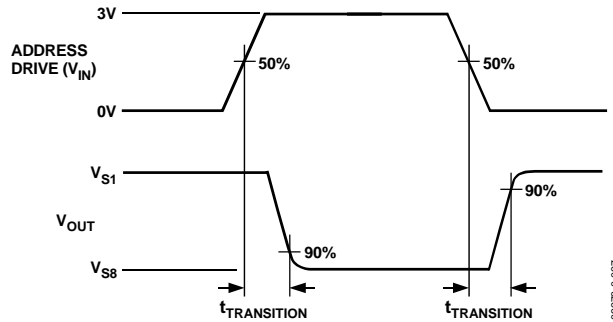
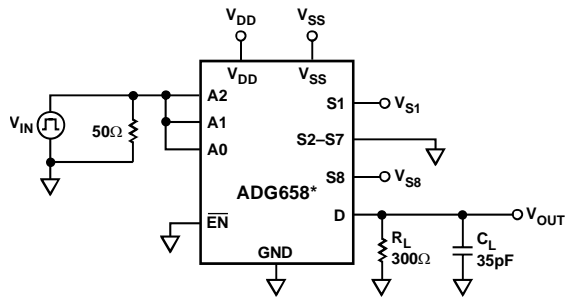


Figure 25. Switching Time of Multiplexer, $t_{\text{TRANSITION}}$

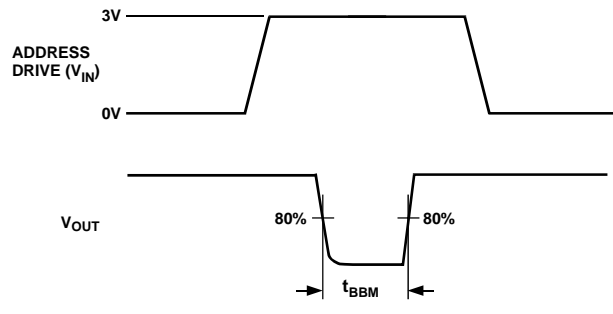
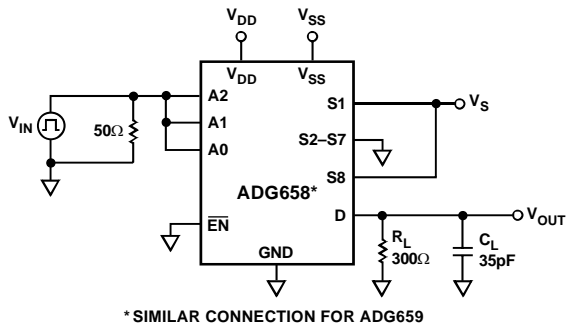


Figure 26. Break-Before-Make Delay, t_{BBM}

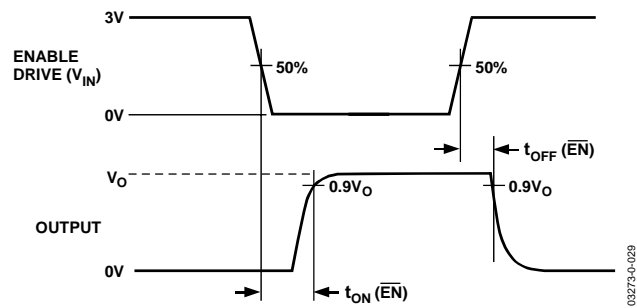
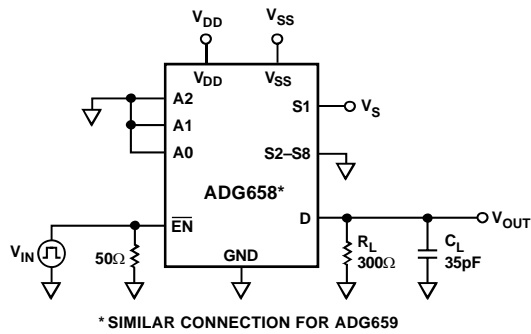


Figure 27. Enable Delay, $t_{ON}(\overline{EN})$, $t_{OFF}(\overline{EN})$

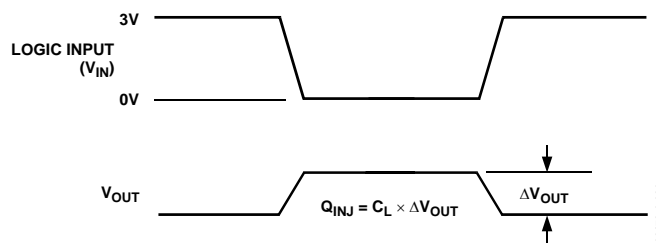
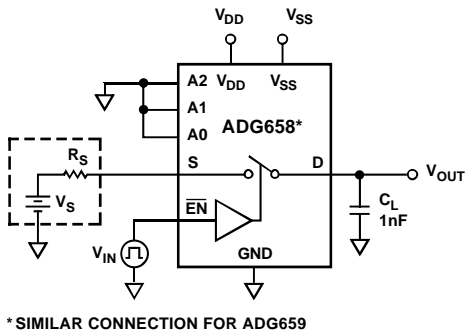


Figure 28. Charge Injection

ADG658/ADG659

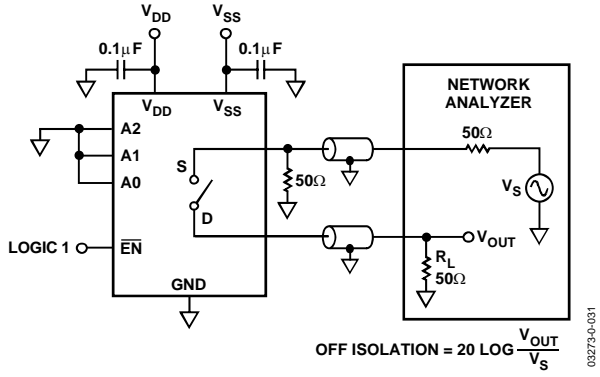


Figure 29. Off Isolation

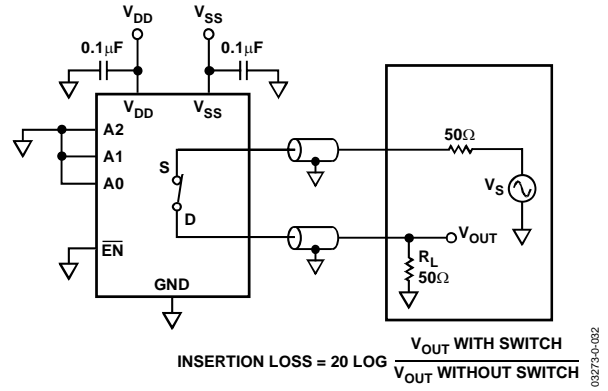


Figure 30. Bandwidth

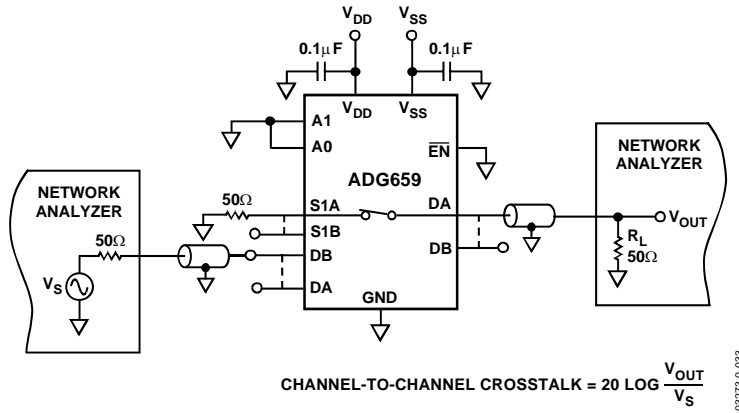


Figure 31. Channel-to-Channel Crosstalk

OUTLINE DIMENSIONS

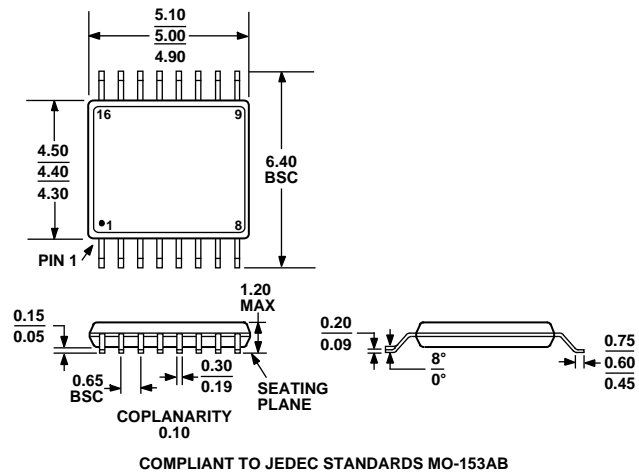


Figure 32. 16-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-16)
Dimensions shown in millimeters

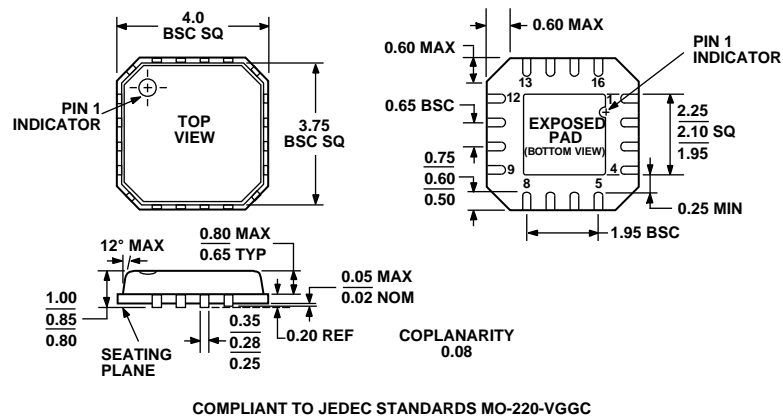
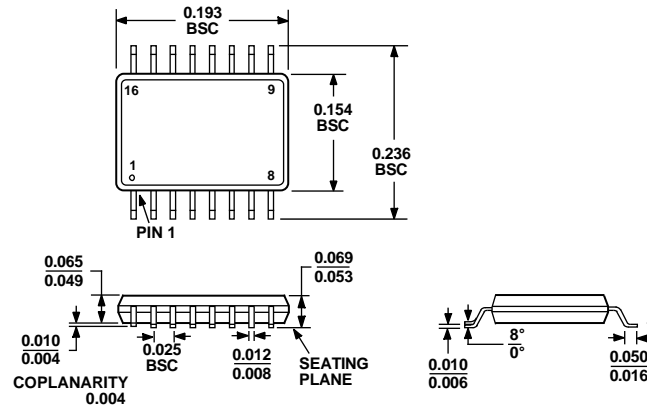


Figure 33. 16-Lead Lead Frame Chip Scale Package [LFCSP]
(CP-16-4)
Dimensions shown in millimeters

ADG658/ADG659



COMPLIANT TO JEDEC STANDARDS MO-137AB

Figure 34. 16-Lead Shrink Small Outline Package [QSOP] (RQ-16)

Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG658YRU	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YRU-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YRUZ ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YRUZ-REEL7 ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG658YCP	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG658YCP-REEL7	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG658YCPZ ¹	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG658YRQ	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG658YRQ-REEL	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG658YRQZ ¹	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG658YRQZ-REEL7 ¹	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRU	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YRU-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YRUZ ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YRUZ-REEL7 ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659WYRUZ-REEL7 ^{1,2}	-40°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG659YCP	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG659YCPZ ¹	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG659YCPZ-REEL7 ¹	-40°C to +85°C	16-Lead Lead Frame Chip Scale Package [LFCSP]	CP-16
ADG659YRQ	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRQ-REEL	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRQ-REEL7	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16
ADG659YRQZ ¹	-40°C to +125°C	16-Lead Shrink Small Outline Package [QSOP]	RQ-16

¹ Z = RoHS Compliant Part.

² Qualified for automotive.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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